# VS-UFB211FA40

**Vishay Semiconductors** 

## **Insulated Ultrafast Rectifier Module, 210 A**



400 V

210 A

40 ns

Modules - Diode FRED Pt®

SOT-227

**PRODUCT SUMMARY** 

 $V_{\mathsf{R}}$ 

I<sub>F(AV)</sub> per module at T<sub>C</sub> = 133 °C

t<sub>rr</sub>

Туре

Package

www.vishay.com

#### **FEATURES**

- Two fully independent diodes
- Fully insulated package
- Ultrafast, soft reverse recovery, with high **RoHS** operation junction temperature ( $T_J$  max. = 175 °C) <sup>COMPLIANT</sup>
- Low forward voltage drop
- Optimized for power conversion: welding and industrial SMPS applications
- · Easy to use and parallel
- Industry standard outline
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### DESCRIPTION

The VS-UFB211FA40 insulated modules integrate two state of the art ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The diodes structure, and its life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Cathode to anode voltage	V <sub>R</sub>		400	V		
Continuous forward current per diode	I <sub>F</sub> <sup>(1)</sup>	T <sub>C</sub> = 90 °C	210	А		
Single pulse forward current per diode	I <sub>FSM</sub>	T <sub>C</sub> = 25 °C	1300	A		
Maximum power dissipation per module	PD	$T_{\rm C} = 90 \ ^{\circ}{\rm C}$	531	W		
RMS isolation voltage	V <sub>ISOL</sub>	Any terminal to case, t = 1 minute	2500	V		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C		

#### Note

(1) Maximum continuous forward current must be limited to 100 A to do not exceed the maximum temperature of power terminals.

<b>ELECTRICAL SPECIFICATIONS PER DIODE</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	400	-	-		
Forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 100 A	-	1.06	1.24	V	
		I <sub>F</sub> = 100 A, T <sub>J</sub> = 175 °C	-	0.85	0.95		
Reverse leakage current	I <sub>RM</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	1.3	50	μA	
		T <sub>J</sub> = 175 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	0.36	4	mA	
Junction capacitance	CT	V <sub>R</sub> = 400 V	-	100	-	pF	

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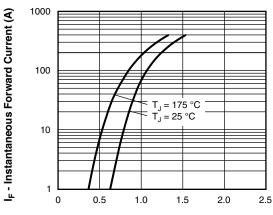


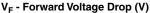
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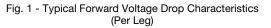
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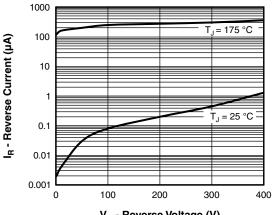
<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONE	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	õs, V <sub>R</sub> = 30 V	-	40	-	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	93	-	ns A nC
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 150 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	172	-	
Peak recovery current I <sub>RRM</sub>		T <sub>J</sub> = 25 °C		-	10.5	-	
	IRRM	T <sub>J</sub> = 125 °C		-	20.2	-	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	490	-	
		T <sub>J</sub> = 125 °C		-	1740	-	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Junction to case, single leg conducting	В		-	-	0.32		
Junction to case, both leg conducting	– R <sub>thJC</sub>		-	-	0.16	°C/W	
Case to heat sink	R <sub>thCS</sub>	Flat, greased surface	-	0.1	-		
Weight			-	30	-	g	
Mounting torque			-	-	1.3	Nm	
Case style			SOT-227				



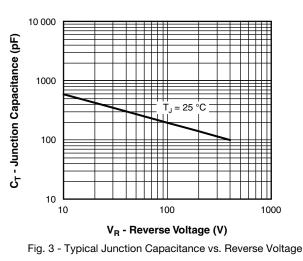






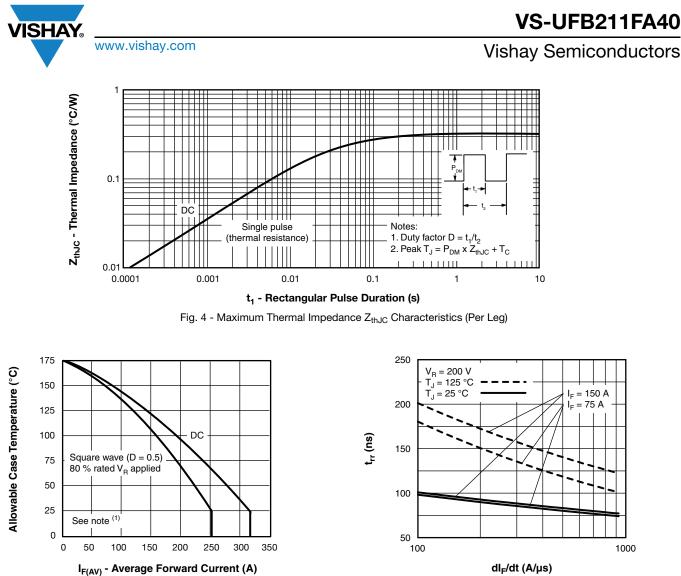
V<sub>R</sub> - Reverse Voltage (V)

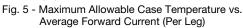
Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

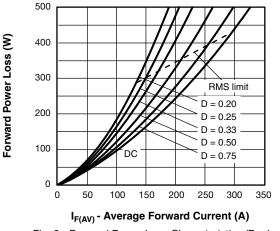


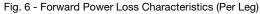
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#### Note

(1) Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

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5000

4500

4000

3500

3000

2500

2000

1500

1000

500

0

100

(Ju C)

ð

V<sub>R</sub> = 200 V

T<sub>J</sub> = 125 °C

I<sub>F</sub> = 150 A

 $I_{F} = 75 \text{ A}$ 

T<sub>1</sub> = 25 °C

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Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

dl<sub>F</sub>/dt (A/µs)

Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

## VS-UFB211FA40



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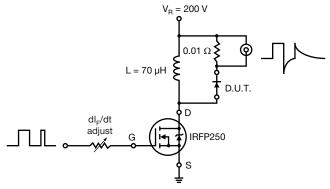
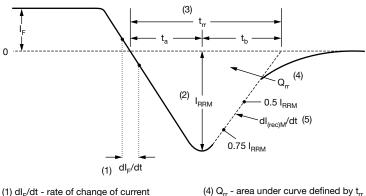


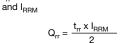
Fig. 9 - Reverse Recovery Parameter Test Circuit



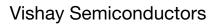
(1) dI<sub>F</sub>/dt - rate of change of current through zero crossing

(2) I<sub>RRM</sub> - peak reverse recovery current

 $\begin{array}{l} \text{(3) } t_{rr} \text{ - reverse recovery time measured} \\ \text{from zero crossing point of negative} \\ \text{going I}_{\text{F}} \text{ to point where a line passing} \\ \text{through } 0.75 \text{ I}_{\text{RRM}} \text{ and } 0.50 \text{ I}_{\text{RRM}} \\ \text{extrapolated to zero current.} \end{array}$ 



- (5)  $dI_{(rec)M}/dt$  peak rate of change of current during  $t_b$  portion of  $t_{rr}$
- Fig. 10 Reverse Recovery Waveform and Definitions





## **ORDERING INFORMATION TABLE**

Device code	VS-	UF	в	211	F	Α	40
		<u> </u>		<u> </u>		<u> </u>	
	1	2	3	4	5	6	$\overline{7}$
	1 - Vishay Semiconductors product						
	2 -	Ultr	afast ree	ctifier			
	3 -	Ultr	afast Pt	diffused	1		
	4 -	Cur	rent rati	ng (211	= 210 A	A)	
	5 -	Circ	uit conf	iguratior	ר (2 sep	arate di	iodes, p
	6 -	Pac	kage in	dicator (	SOT-22	27 stand	lard ins
	7 -	Volt	age rati	ng (40 =	= 400 V)	)	

Quantity per tube is 10, M4 screw and washer included

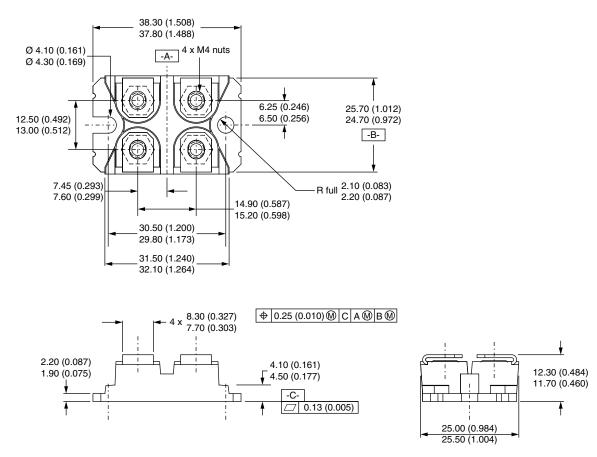
CIRCUIT CONFIGURATION						
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
2 separate diodes, parallel pin-out	F	Lead Assignment 4 1 1 1 1 1 1 1 1 1 1 1 1 1				

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95423						
Packaging information	www.vishay.com/doc?95425					



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## DIMENSIONS in millimeters (inches) SOT-227 Gen 2

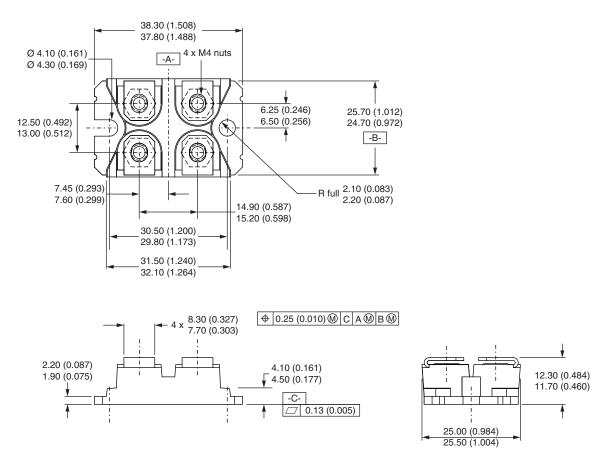


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**SOT-227 Generation II** 

### **DIMENSIONS** in millimeters (inches)



Note

• Controlling dimension: millimeter



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